

10/685013

CofR



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jack o. Chu, et al.

Docket: 16971

Patent No.: 6,949,761

Dated: April 21, 2006

Issued: September 27, 2005

**For: STRUCTURE FOR AND METHOD OF
FABRICATING A HIGH-MOBILITY
FIELD-EFFECT TRANSISTOR**

**Certificate
MAY 02 2006
of Correction**

**Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450**

REQUEST FOR CERTIFICATE OF CORRECTION

Sir:

**It appears that errors have been introduced in the
course of printing the Patent issued in the above application, and it is
respectfully requested that the Commissioner issue a Certificate of
Correction in the following respects:**

Title Page:

"(75) Jack O. Chu, Manhasser Hills, NY"

should read

-(75) Jack O. Chu, Manhasset Hills, NY --

MAY 3 2006

Column 9, Line 28, Claim 1:

“a Si cap layer on top of said top”

should read

-- a Si cap layer under tensile strain on top of said top --

Column 9, Line 47, Claim 3:

“between 2 to 20nm” should read -- between 2 nm to nm. --

Column 10, Line 28, Claim 8:

“a Si cap layer on top of said top”

should read

-- a Si cap layer under tensile strain on top of said top --

Column 11, Line 33, Claim 17:

“a Si cap layer on top of said top”

should read

-- a Si cap layer under tensile strain on top of said top --

Column 13, Line 2, Claim 29:

“a Si cap layer on top of said top”

should read

-- a Si cap layer under tensile strain on top of said top --

Column 13, Line 46, Claim 34:

“a Si cap layer on top of said top”

should read

-- a Si cap layer under tensile strain on top of said top --

MAY 3 2006

Column 14, Line 44, Claim 41:
"a Si cap layer on top of said top"

should read

-- a Si cap layer under tensile strain on top of said top --

Column 15, Line 57, Claim 51:
"a Si cap layer on top of said top"

should read

-- a Si cap layer under tensile strain on top of said top --

Column 16, Line 61, Claim 58:
"a Si cap layer on top of said top"

should read

-- a Si cap layer under tensile strain on top of said top --

Respectfully submitted,



Steven Fischman, Esq.
Reg. No. 34,594

Scully, Scott, Murphy & Presser
400 Garden City Plaza, Suite 300
Garden City, New York 11530
(516) 742-4343

MAY 3 2006

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 3

PATENT NO : 6,949,761
APPLICATION NO : 10/685,013
ISSUE DATE : September 27, 2005
INVENTOR(S) : Jack O. Chu, et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page:

“(75) Jack O. Chu, Manhasset Hills, NY”

should read

–(75) Jack O. Chu, Manhasset Hills, NY –

Column 9, Line 28, Claim 1:

“a Si cap layer on top of said top”

should read

– a Si cap layer under tensile strain on top of said top –

Column 9, Line 47, Claim 3:

“between 2 to 20nm” should read -- between 2 nm to nm. --

Column 10, Line 28, Claim 8:

“a Si cap layer on top of said top”

should read

– a Si cap layer under tensile strain on top of said top –

MAILING ADDRESS OF SENDER:

Scully, Scott, Murphy & Presser
400 Garden City Plaza, Suite 300
Garden City, New York 11530

PATENT No. 6,949,761

No. of additional copies

1 3 2006

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 2 of 3

PATENT NO : 6,949,761
APPLICATION NO : 10/685,013
ISSUE DATE : September 27, 2005
INVENTOR(S) : Jack O. Chu, et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 11, Line 33, Claim 17:
"a Si cap layer on top of said top"

should read

-- a Si cap layer under tensile strain on top of said top --

Column 13, Line 2, Claim 29:
"a Si cap layer on top of said top"

should read

-- a Si cap layer under tensile strain on top of said top --

Column 13, Line 46, Claim 34:
"a Si cap layer on top of said top"

should read

-- a Si cap layer under tensile strain on top of said top --

MAILING ADDRESS OF SENDER:

Scully, Scott, Murphy & Presser
400 Garden City Plaza, Suite 300
Garden City, New York 11530

PATENT No. 6,949,761

No. of additional copies

1

3 2006

**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 3 of 3

PATENT NO : 6,949,761
APPLICATION NO : 10/685,013
ISSUE DATE : September 27, 2005
INVENTOR(S) : Jack O. Chu, et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 14, Line 44, Claim 41:
"a Si cap layer on top of said top"

should read

-- a Si cap layer under tensile strain on top of said top --

Column 15, Line 57, Claim 51:
"a Si cap layer on top of said top"

should read

-- a Si cap layer under tensile strain on top of said top --

Column 16, Line 61, Claim 58:
"a Si cap layer on top of said top"

should read

-- a Si cap layer under tensile strain on top of said top --

MAILING ADDRESS OF SENDER:

Scully, Scott, Murphy & Presser.
400 Garden City Plaza, Suite 300
Garden City, New York 11530

PATENT No. 6,949,761

No. of additional copies

1

8/2/06